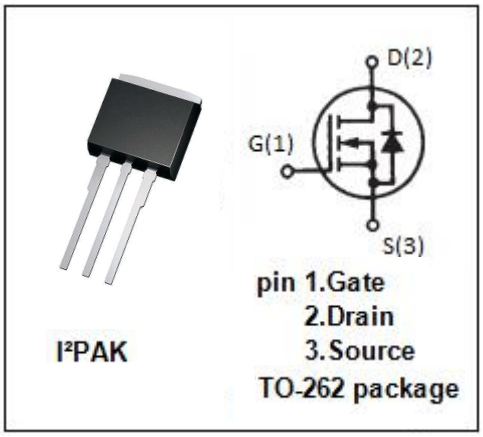
isc N-Channel MOSFET Transistor AOW418

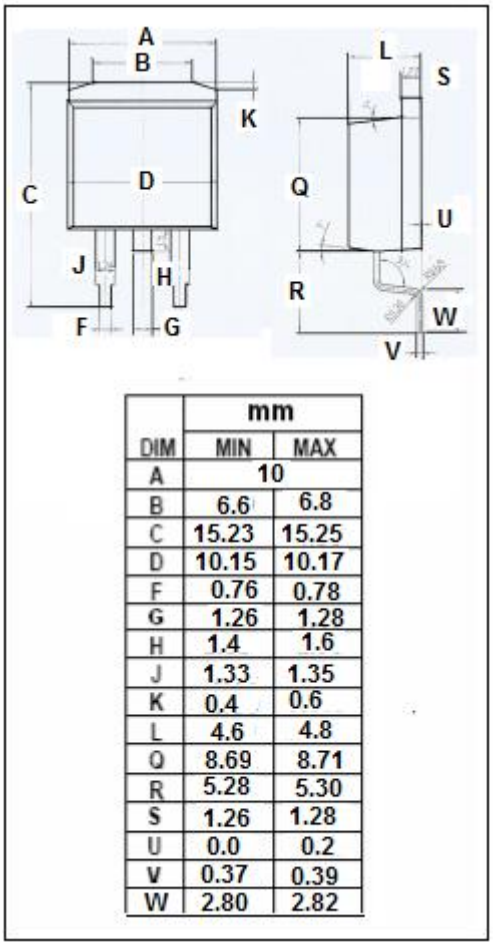
- **FEATURES**
- Drain Current –I_D= 105A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 100V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 10mΩ(Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



- **DESCRITION**
- Be suitable for synchronous rectification for server and general purpose applications

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±25	V
I_D	Drain Current-Continuous	105	A
I_{DM}	Drain Current-Single Pulsed	280	A
P_D	Total Dissipation @T_C=25℃	333	W
T_j	Max. Operating Junction Temperature	-55~175	℃
T_{stg}	Storage Temperature	-55~175	℃



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.45	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D = 250 μ A	100		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D = 250 μ A	2.6	3.9	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 20A V_{GS}= 10V; I_D= 20A;T_J= 125℃		10 18	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±25V;V_{DS}= 0V		±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= 100V; V_{GS}= 0V V_{DS}= 100V; V_{GS}= 0V;T_J= 55℃		10 50	μ A
V_{SD}	Diode forward voltage	Is= 1A; V_{GS} = 0V		1	V